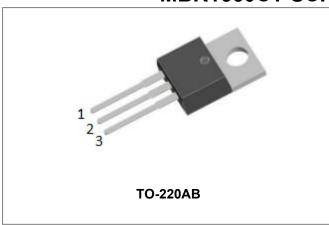






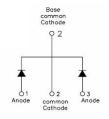
# **MBR1660CT SCHOTTKY RECTIFIER**



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

### **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

#### Maximum Ratings(Tc =25°C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	60	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	Tc=143°C, In DC	8(Per Leg) 16(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	150	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 8A, Pulse, T <sub>J</sub> = 25 °C	0.65	0.78	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.015	1.0	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 \text{ °C}$ $f_{SIG} = 1MHz$	180	400	pF
Series Inductance(Per Leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>th(j-c)</sub>	DC operation	1.2	°C/W
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			

# **Ratings and Characteristics Curves**

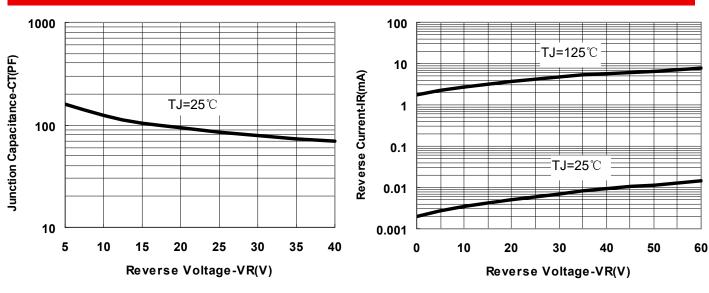


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

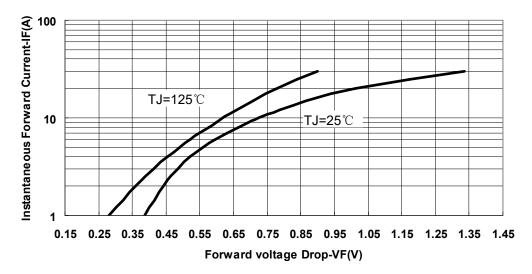


Fig.3-Typical Instantaneous Forward Voltage Characteristics

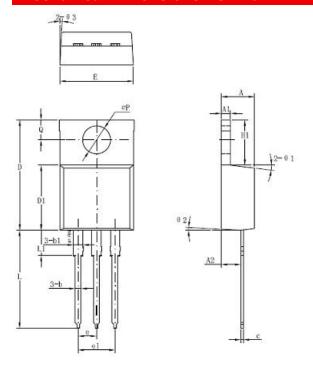
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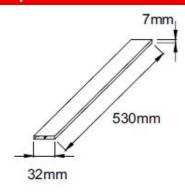


#### **Mechanical Dimensions TO-220AB**



Symbol	Dimensions in millimeters			
	Min	Typical	Max	
Α	3.56	-	4.83	
A1	0.51	-	1.4	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
С	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E	9.65	-	10.67	
е	-	2.54	-	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.7	-	14.73	
L1	-	-	6.35	
ФР	-	3.56	-	
Q	2.54	-	3.43	

## **Tube Specification**



## **Marking Diagram**



Where XXXXX is YYWWL

 MBR
 = Device Type

 16
 = Forward Current (16A)

 60
 = Reverse Voltage(60V)

 CT
 = Configuration

 SSG
 = SSG

Cautions: Molding resin
Epoxy resin UL:94V-0

## **Ordering Information**

Device	Package	Shipping	
MBR1660CT	TO-220AB (Pb-Free)	50 pcs/ tube	

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